## DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION

DOCKET NO. <u>TS01-1132</u>

As a below named Inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name;

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled Complementary Metal Oxide Semiconductor Transistor Technology Using Selective Epitaxy Of A Strained Silicon Germanium Layer

the specification of which (check one)	BEST AV	AILABLE COPY
X is attached hereto.		WE WELL COPY
was filed on		
Application Serial No.	•	
and was amended on	anlicahla)	
I hereby state that I have reviewed and us amended by any amendment referred to a	iderstand the contents of the a above.	bove Identified specification including the claims, as
Lacknowledge the duty to disclose information 37. Code of Federal Regulations, §	nation which is material to the 1.56(a).	examination of this application in accordance with
I hereby claim foreign priority benefits u inventor's certificate listed below and ha having a filing date before that of the app	nder Title 35. United States Cover also identified below any for plication on which priority is continuously and the control of the control o	ode \$119 of any foreign application(s) for patent or oreign application for patent or inventor's certificate laimed:
Prior Foreign Application(s)		Priority Claimed:
(Number)	(Country)	(Day/Month/Year Filed)
(Number)	(Country)	(Day/Month/Year Filed)
I hereby claim the benefit under Title 35 as the subject matter of each of the claim manner provided by the first paragraph of information as defined in Title 37, Code application and the national or PCT inte	, United States Code §120 of a six of this application is not dis of Title 35, United States Code of Federal Regulations, §1.56 mational filing date of this appropriate of the same control of the same contr	any United States application(s) listed below and, insofar closed in the prior United States application in the t, §112, I acknowledge the duty to disclose material (a) which occurred between the filing date of the prior olication:
(Application Serial No.)		
I hereby declare that all statements made belief are believed to be true; and furthe the like so made are punishable by fine and that such willful false statements made	e herein of my own knowledge ir that these statements were in or imprisonment, or both, und ay jeopardize the validity of th	e are true and that all statements made on information and ade with the knowledge that willful false statements and er Section 1001 of Title 18 of the United States Code e application or any patent issued thereon.
POWER OF ATTORNEY: As a named application and transact all business in t	inventor, I hereby appoint the he Patent and Trademark Offi	following attorney(s) and/or agent(s) to prosecute this ce connected therewith. (list name & registration no.)
GEORGE O. SAILE. (Reg. No.	. 19,572), STEPHEN B.	ACKERMAN (Reg. No. 37,761)
Send Correspondence to: 20 MCINTO	SH DRIVE, POUGHKEEPSI	E; NEW YORK 12603
Direct telephone Calls to: (name & teleph	none number) GEORGE 0. S	AILE NEW YURK 845 452 3803  November 27, 2001.
YEE-CHIA YEO Full name of sole or first inventor Yeachia Yeo		November 27, 2001.  Date ,
Inventor's signature  980 OHLONE AVE #985,	ALBANY, CA, 94706	, ush.
Residence SINGAPORE		
Citizenship		
121 Park Ave. Rd. 3, Science-Base Post Office Address	d Industrial Park, Hsin-Chu,	Taiwan, Republic of China

Talwan 421. 2.5.

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3FL., No. 32 Lane 284 Shiangshang N Rd shi Chin, Taichung
Republic of China : Talwan
Te public of
121 Park Ave. Rd. 3. Science-Based Industrial Park, Hsin-Chu, Taiwan, Republic of China
121 Park AVR. KG. 3. Science 445
FU-LIANG VANG
ill name of third inventor
Inventor's signment TATIMAN
18-3 No. 68 Viniversity Road, Hisin-Chu City, 1911 Verilly,
Republic of China, Taiwan
Citizenship   Penumic of China
121 Park Ave. Rd. 3. Science-Based Industriat Park. Haln-Chu, Taiwan, Republic of China Post Office Address
CHEN MING HU Date
Full name of fourth inventor / [ illa 7.01
Inventor's Signature
Inventor's Signature 9, Creation Rd. 1. Sugare - Based Industrial Park. Hsin-Chin
Residence
U.S. A.
Citizenship  121 Park Ave. Rd. 3, Science-Based Industrial Park, Hsin-Chu, Talwan, Republic of China
121 Park Ave. Rd. 3, Science-Based industrial Faix, 1150
Date
Full name of fifth inventor
Inventor's rigoriture
Residence
VC2000.45
Citizenship
Post Office Address
Full name of sixth inventor
Inventor's signature
Residence
Citizenship
Part Office Address